

Integrated Photonic Devices

<http://ioe.eei.eng.osaka-u.ac.jp/>

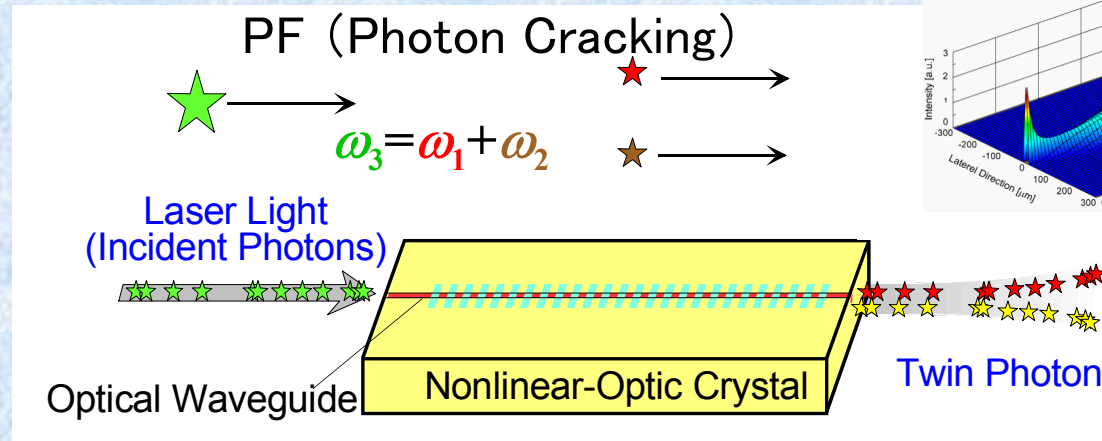
Advanced Integrated Photonic Devices

- IPD for Optical Network
- IPD for Ultrafast Signal Processing
- Quantum Structure Semiconductor Lasers
- Integrated Photonic Sensors
- Integrated Quantum Photonic Devices

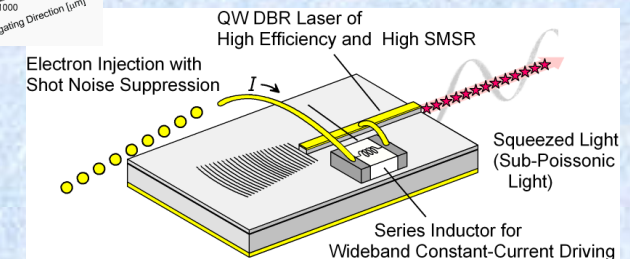
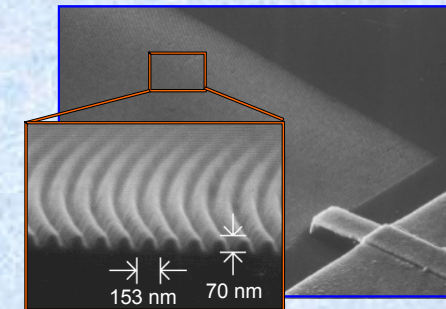
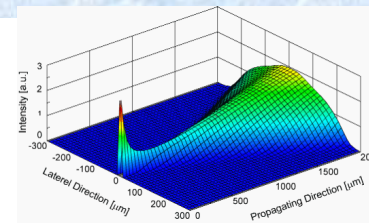


Electron Beam Writing System for Photonics

Design Theory Simulation Fabrication Technology
Device Implementation • Experimental Demonstration

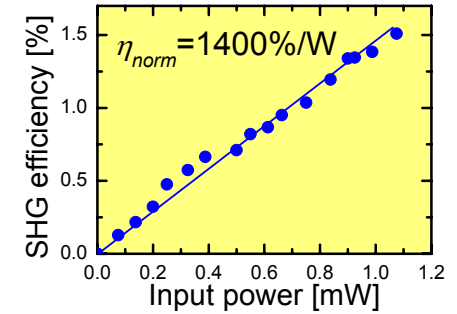
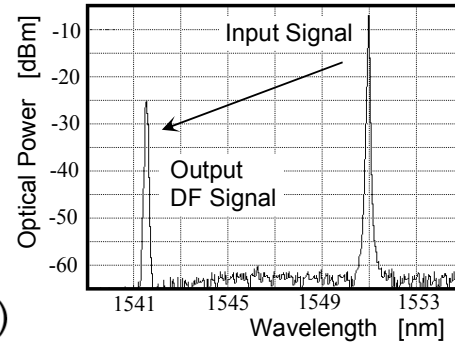
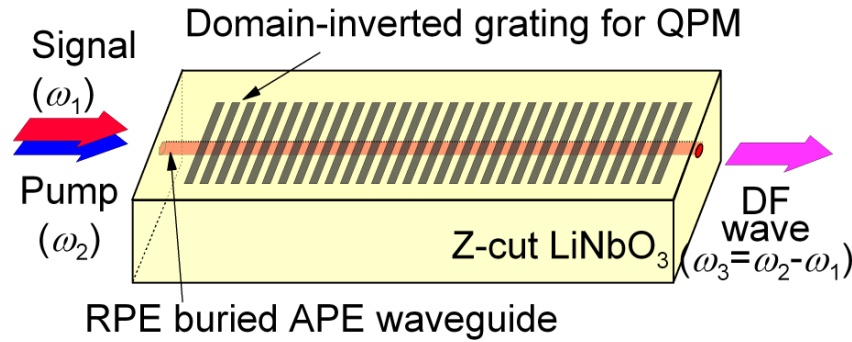


An Example of Quantum Photonic Devices



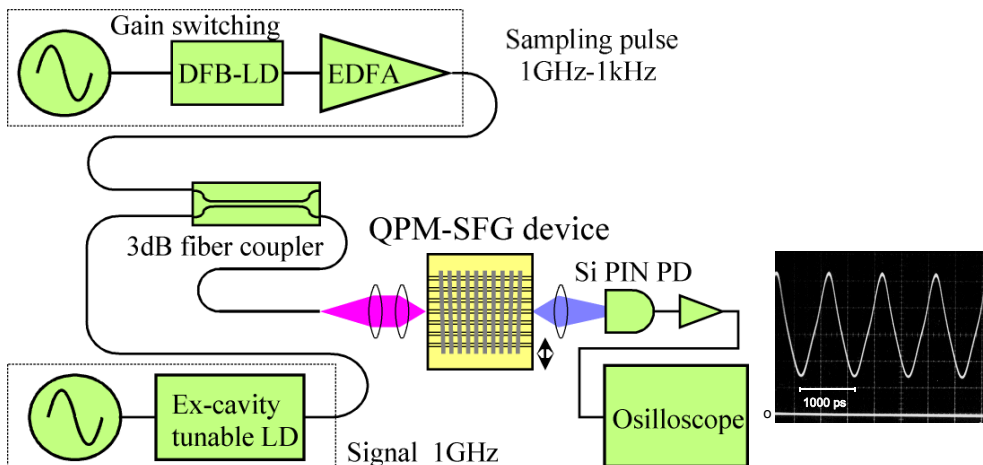
Integrated QW Semiconductor Laser

Waveguide Nonlinear-Optic Devices



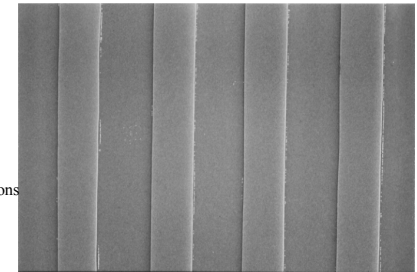
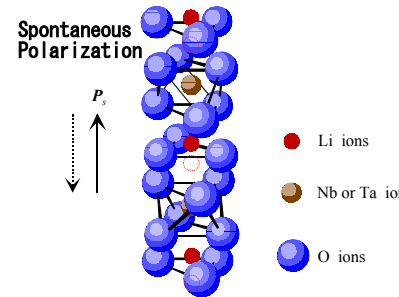
Top Data Efficiency

Wavelength Converters for Photonic Network

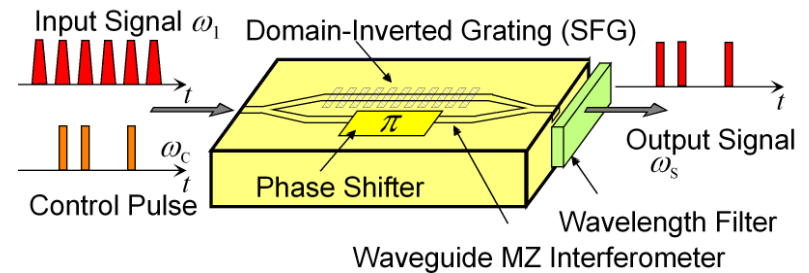


**43%/W
Highest Efficiency**

Optical Sampling Device



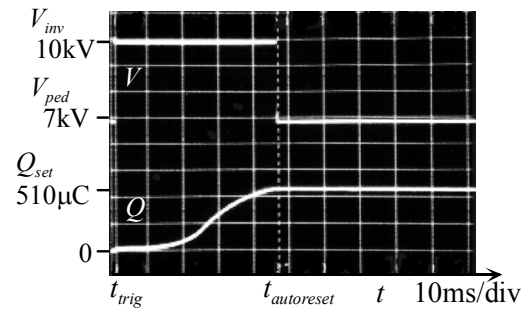
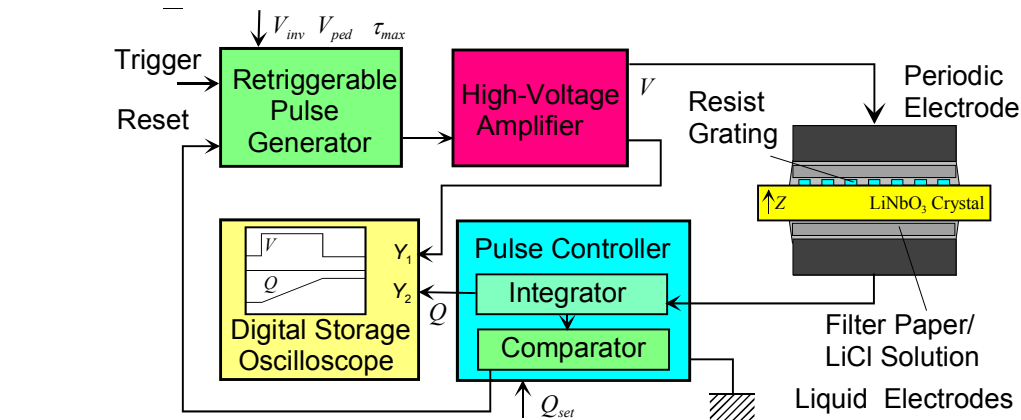
Domain Inverted Grating for QPM



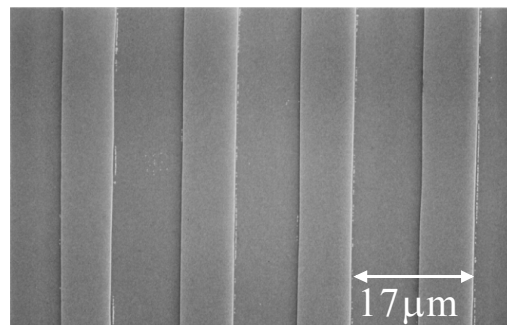
Ultrafast Optical Gate Switch²

Formation of Domain-Inverted Grating for QPM

Voltage Pulse Application using Liquid Electrodes

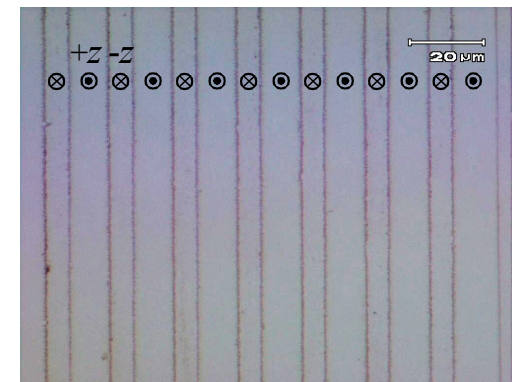
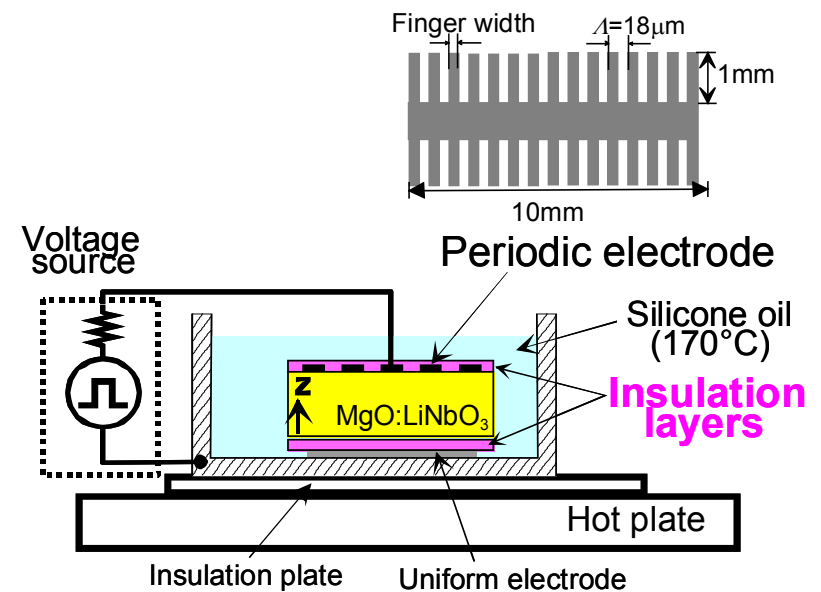


Voltage /Charge Traces



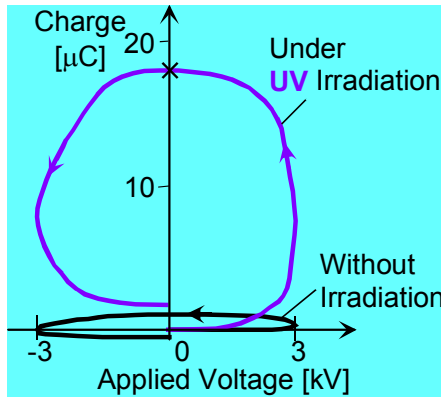
SEM Microphotograph of Domain-Inverted Grating

Voltage Pulse Application using Metal Electrodes



N.Horikawa, T. Tsubouchi, M.Fujimura and T.Suhara, Jpn. J. Appl. Phys., 46, 5178, 2007. 3

QPM Grating Formation in MgO:LiNbO₃ Crystal

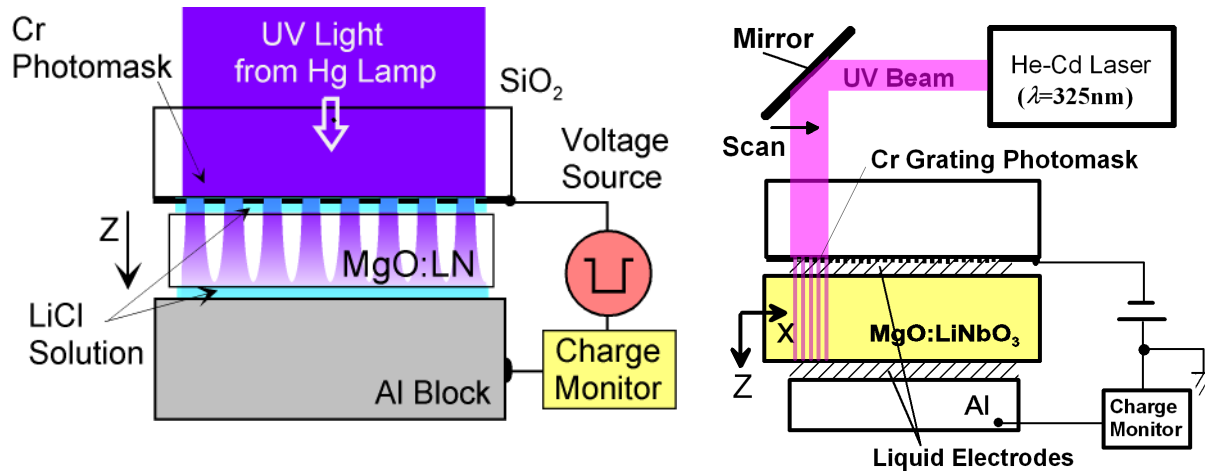
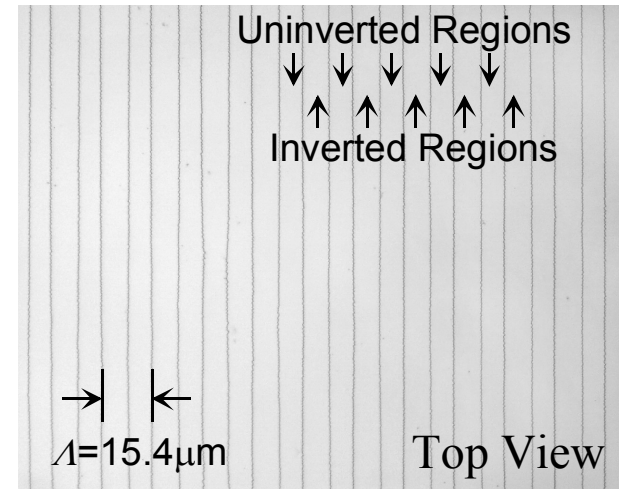


MgO:LiNbO₃
PR damage resistant

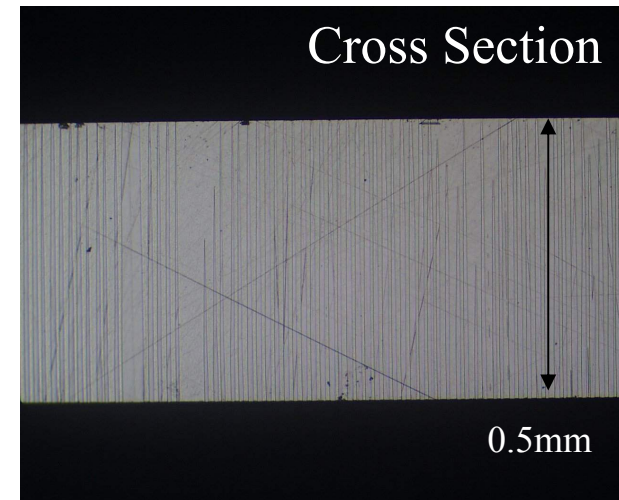
UV Irradiation
 Reduces
 Eff. Coercive Field

Ferroelectric Hysteresis Loop

Room Temperature Resistless Process



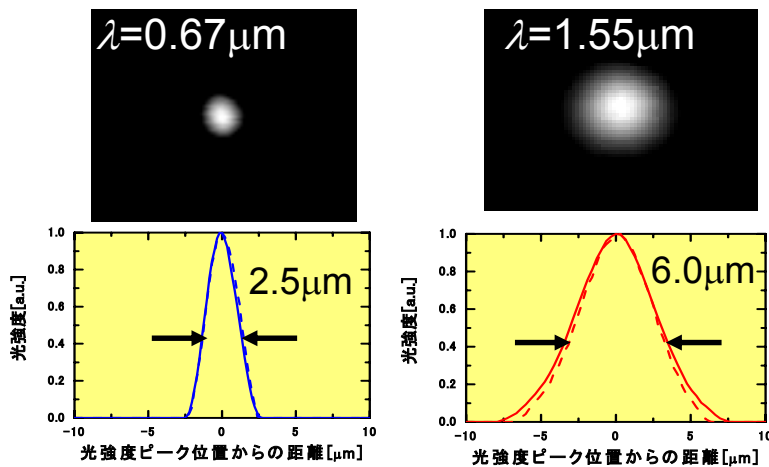
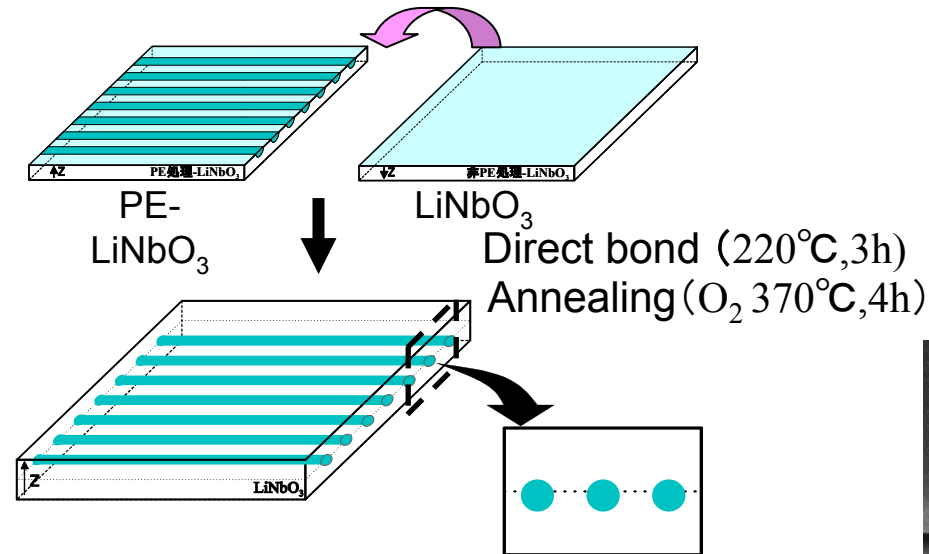
Formation of QPM Grating



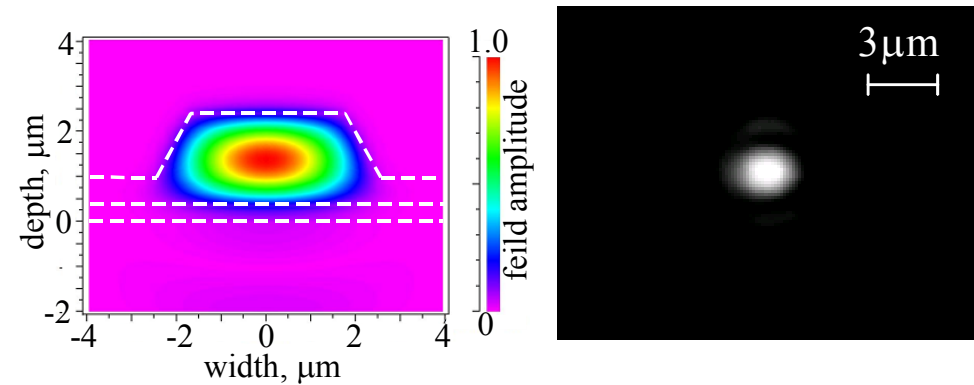
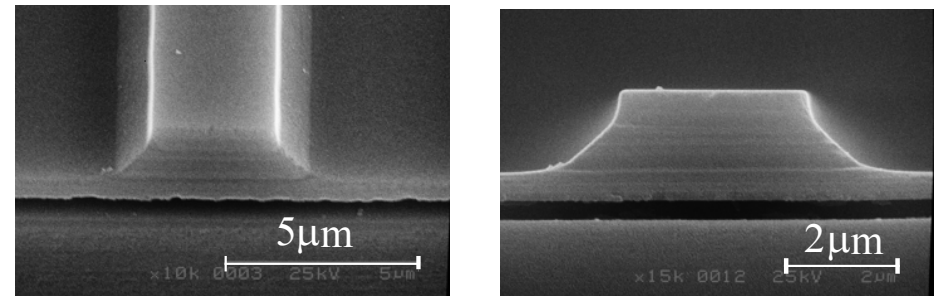
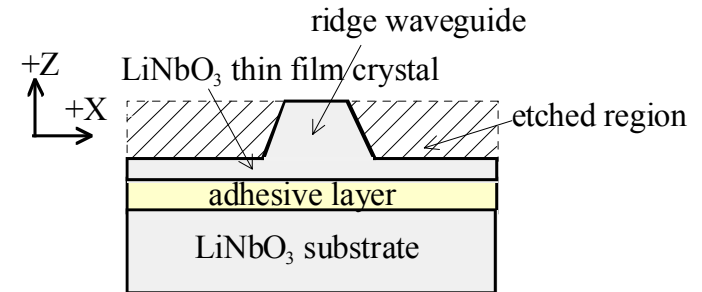
M.Fujimura, T.Sohmura and
 T.Suhara EL. 39, 719, 2003

Fabrication of WG of strong confinement

Buried APE WG fabrication by direct bonding



Ridge WG fabrication by PE accelerated chemical etching

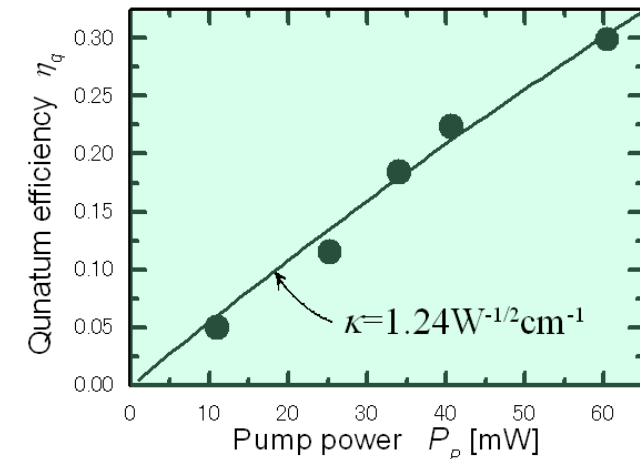
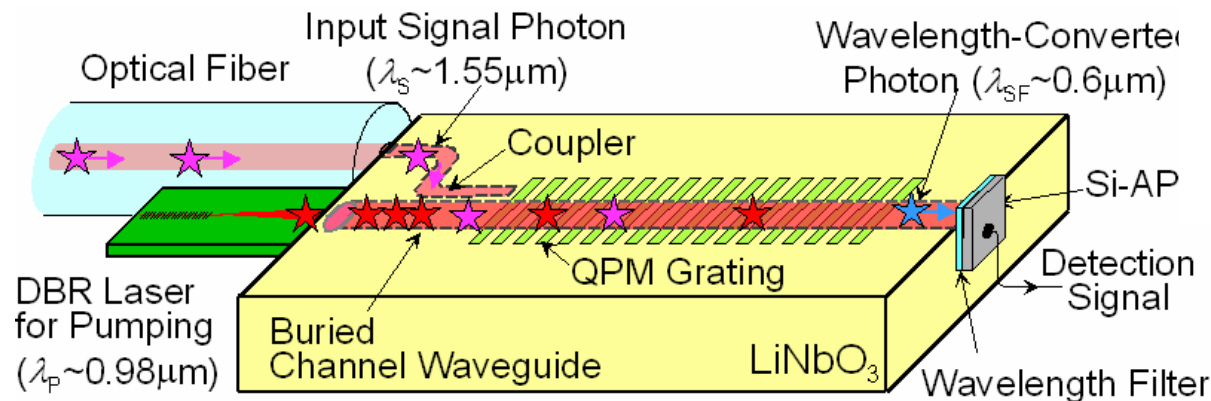


QPM WG SFG upconversion device for single photon detection

QIT Photon transmission through fiber network
Telecom (1.3, 1.5 μm) band Single photon detector

InGaAs-APD involve drawbacks

SFG upconversion to visible and detection by Si-APD



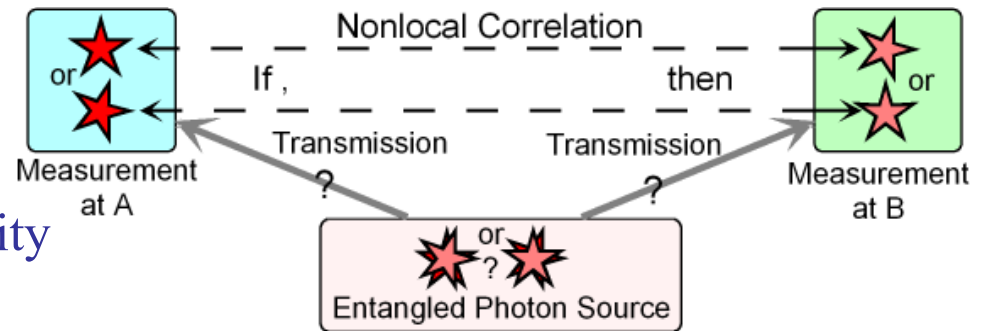
$\eta \sim 30\%$ @ $P_p = 60\text{mW}$

WG QPM Entangled Twin Photon Generation Devices

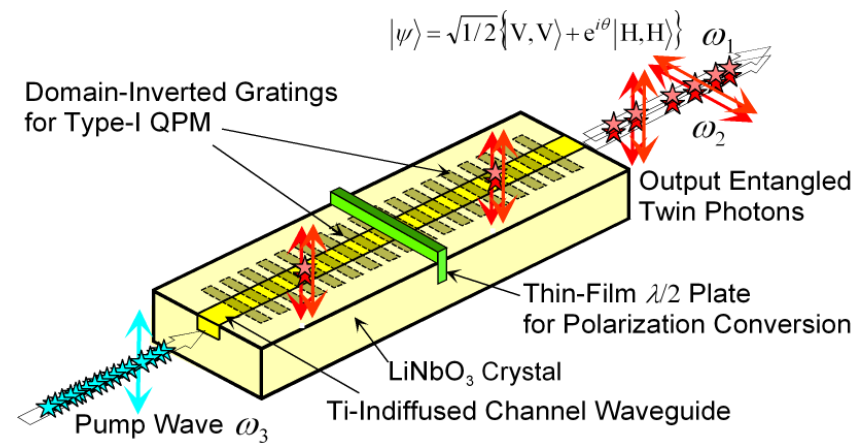
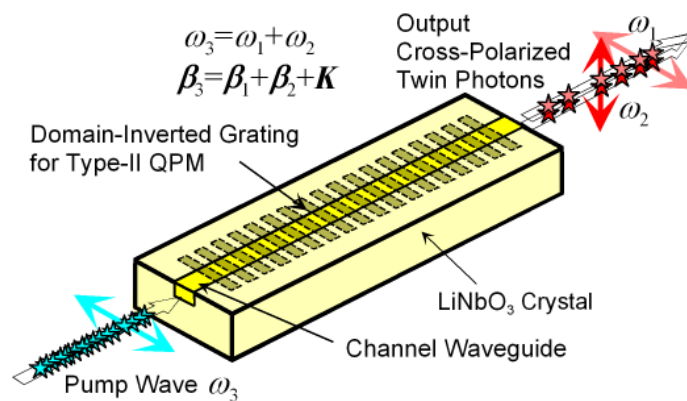
QPM Waveguide NLO Devices for Quantum Information Processing Q-Cryptography, Q-Teleportation, Q-Interface, ...

Quantum Entangled Twin Photons

high efficiency, wavelength flexibility
Integration compatibility



Key Device for QIT



T.Suhara et al. IEEE PTL **19**, p.1093,2007.

J.Kawashima et al., IEEE PTL., **21**, p.566, 2009.

Quantum theory analysis of TPG

Quantum coupled mode eq (H.P.)

$$\frac{d}{dz} a_1(z) = i\kappa A_3 a_2^\dagger(z) \exp(i2\Delta z)$$

$$\frac{d}{dz} a_2(z) = i\kappa A_3 a_1^\dagger(z) \exp(i2\Delta z)$$



Unitary transformation of state (S.P.)

$$|\phi(L)\rangle = T(L)|0,0\rangle = \exp(-iHL)|0,0\rangle$$

$$= \sum_{n=0}^{\infty} \frac{1}{n!} (-iHL)^n |0,0\rangle$$

$$H = i\{a_1^\dagger(\Gamma e^{i\phi} a_2^\dagger - i\Delta a_1) - (\Gamma e^{-i\phi} a_1 + i\Delta a_2^\dagger) a_2\}$$

$$|\phi(L)\rangle = \sum_{n=0}^{\infty} \sqrt{1-|r|^2} r^n |n,n\rangle$$

$$r = \frac{e^{i\phi} (\Gamma/\gamma) \sinh \gamma L}{\cosh \gamma L + i(\Delta/\gamma) \sinh \gamma L}$$

$$\langle N_1(L) \rangle = \langle N_2(L) \rangle = \sinh^2 \Gamma L \{ \sin \Delta L / \Delta L \}^2$$

$$P_{out1} = \hbar \omega_1 \int \langle N_1(L) \rangle (d\omega_1 / 2\pi) \text{ in QPM bandwidth}$$

Photon CCR

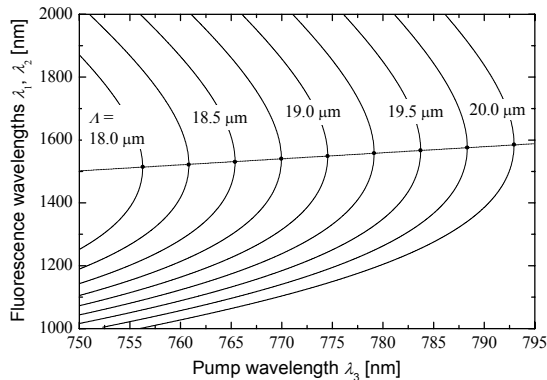
$$P_c(\tau) \propto \text{rect}\left(2 \frac{\delta\omega}{2\pi} \tau\right)$$

Correlation time

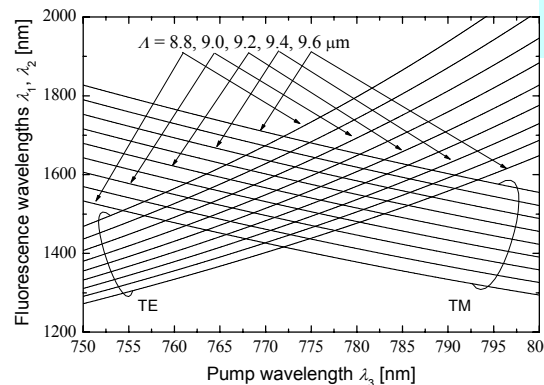
$$\tau_c = (\delta\omega / 2\pi)^{-1} = |n_1 - n_2| L / c$$

$$\langle [\Delta \{N_1(L) - N_2(L)\}]^2 \rangle = 0$$

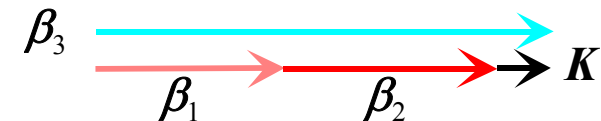
complete correlation



TM → TM+TM Type-I QPM

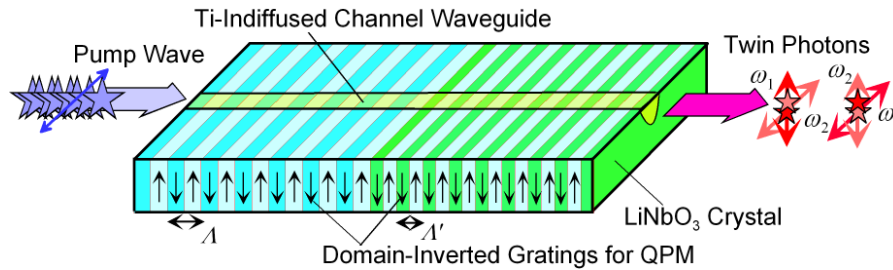


TE → TM+TE Type-II QPM

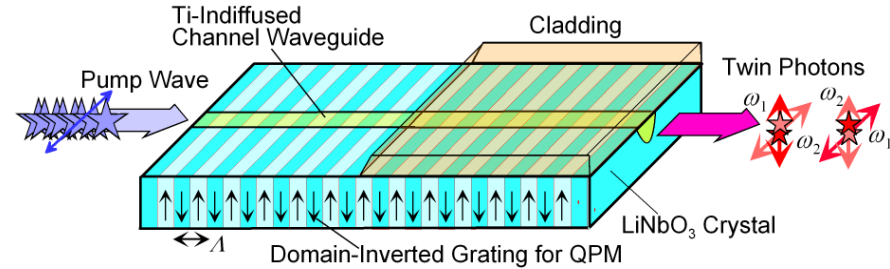


T.Suhara et al. IEEE JQE, **41**, 1203, 2005; **42**, 777, 2006

QPM WG Devices for Generation of Postselection-Free Polarization-Entangled Twin Photons



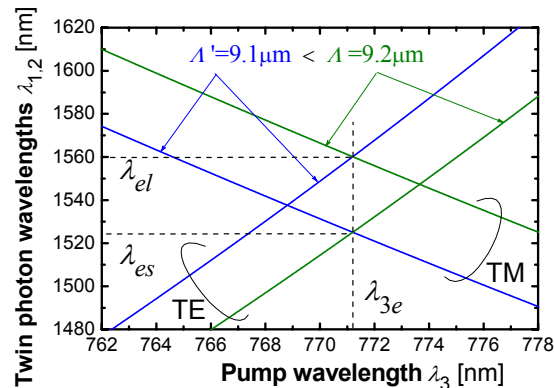
(a) Biperiod type



(b) Clad/Unclad type

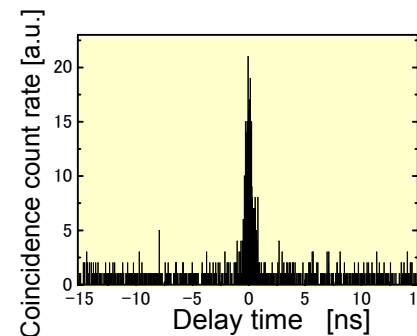
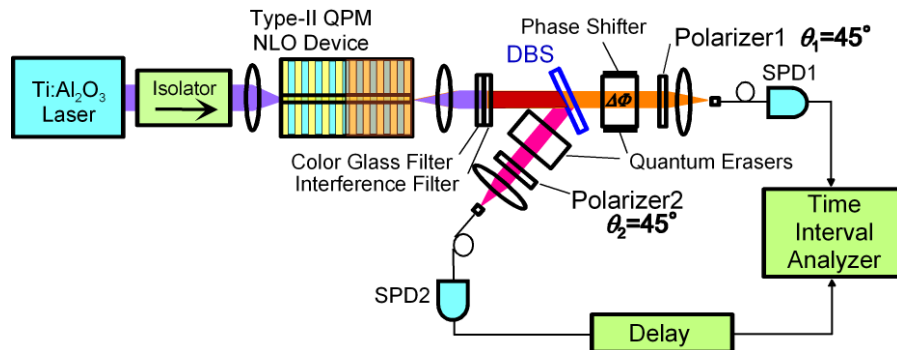
Output state:
$$|\psi\rangle = \frac{1}{\sqrt{2}} \{ |H, V\rangle + \exp(i\Phi_0) |V, H\rangle \}$$

$$\lambda_{el} \lambda_{es} \qquad \lambda_{el} \lambda_{es}$$

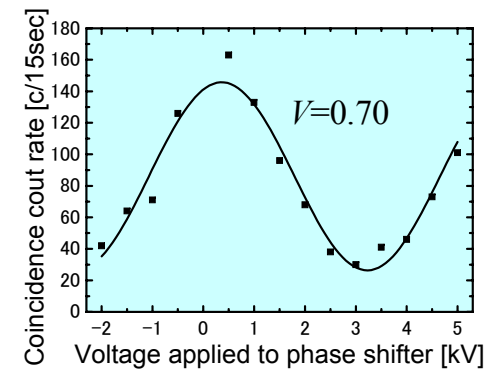


completely separated by DBS

Postselection-free two- λ polarization-entangled twin photons without spurious photon



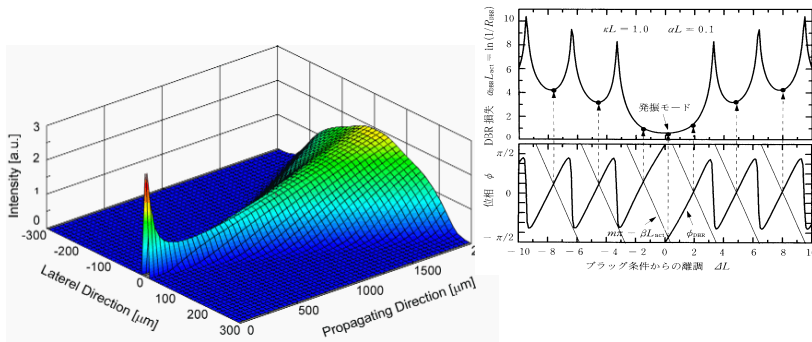
photon correlation



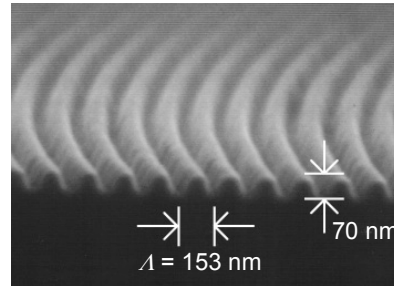
Quantum interference

T.Suhara et al. IEEE PTL 21, 1096 2009.

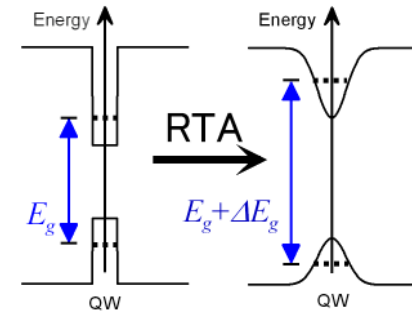
Integrated Semiconductor Lasers



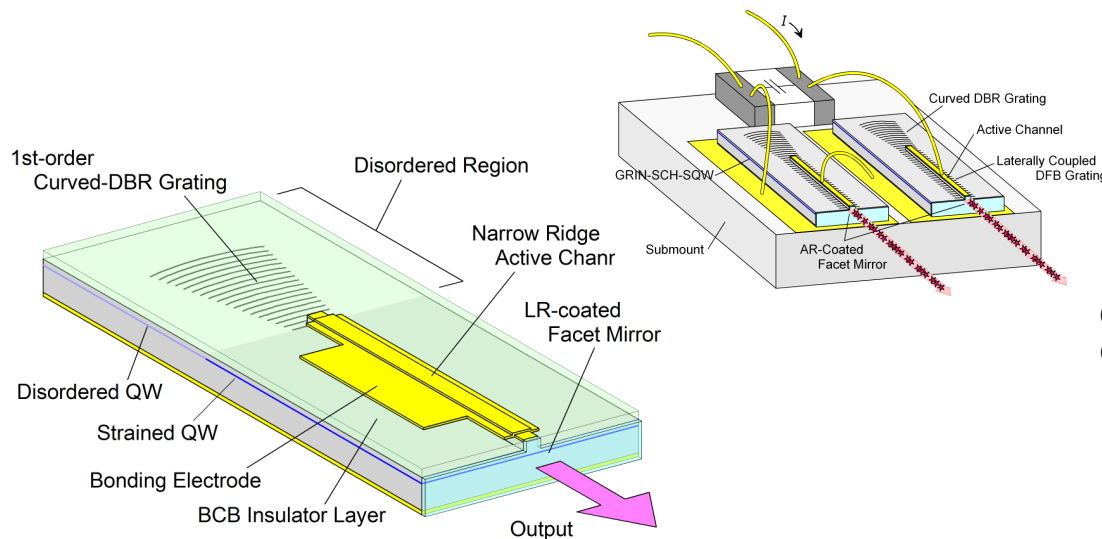
DFB/DBR Laser Simulation



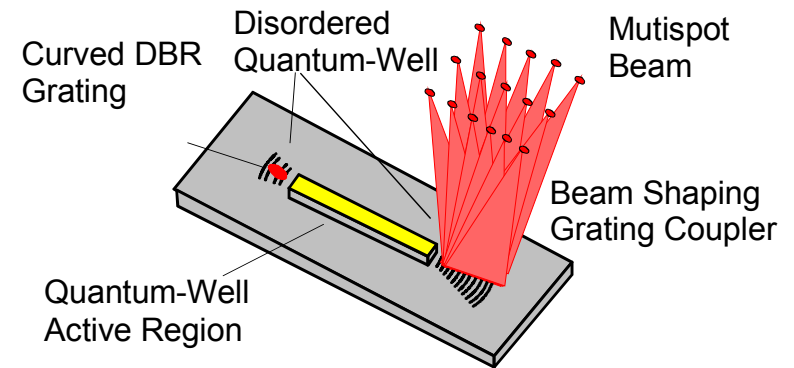
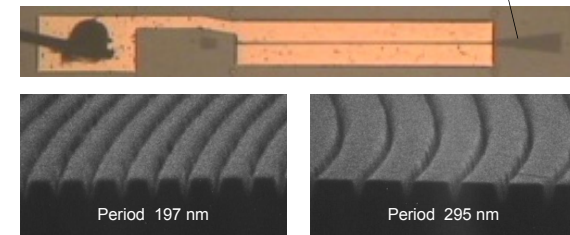
EB Fabrication of Nano Gratings



Selective Disordering of Quantum Well



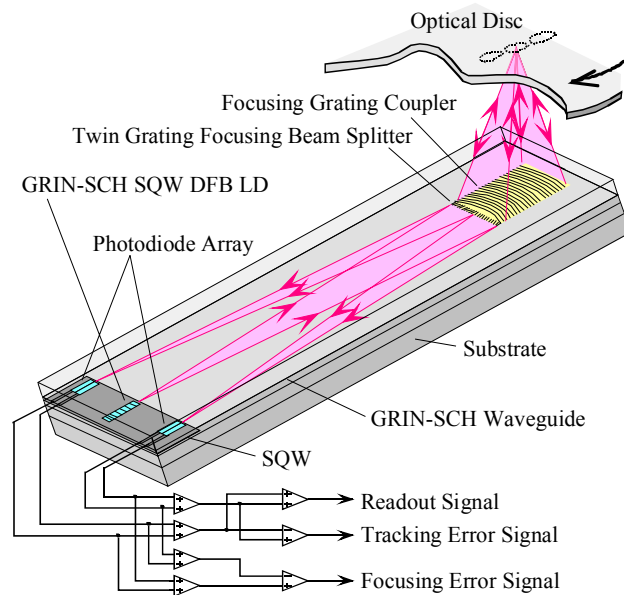
Integrated Semiconductor Lasers for Photonic Network and Quantum-Information



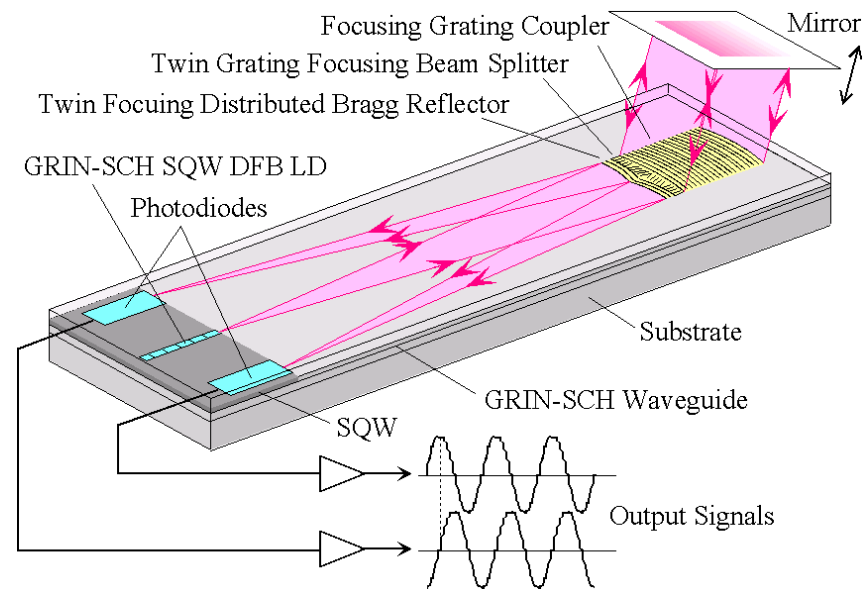
Integrated Semiconductor Lasers for Bio-Sensing

Monolithic Integrated-Optic Sensor Devices

Implementation of IO Sensor Devices by Integration of DFB/DBR Laser, Wavefront Conversion Elements and Photodetectors



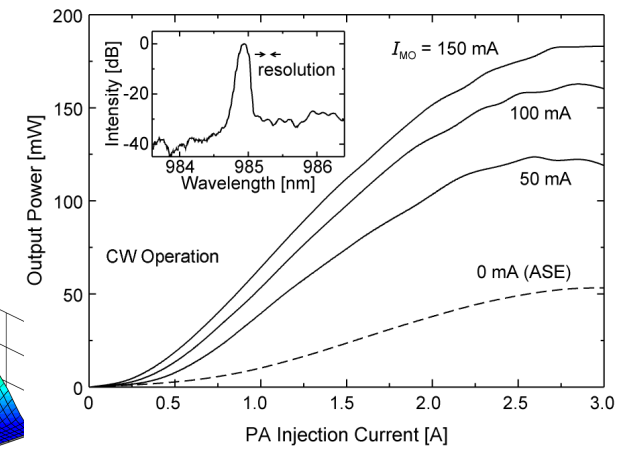
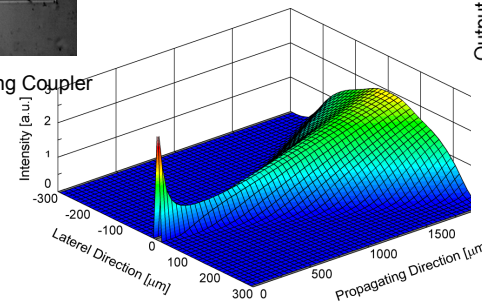
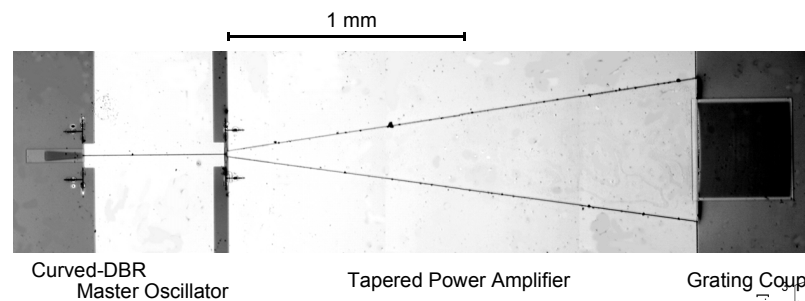
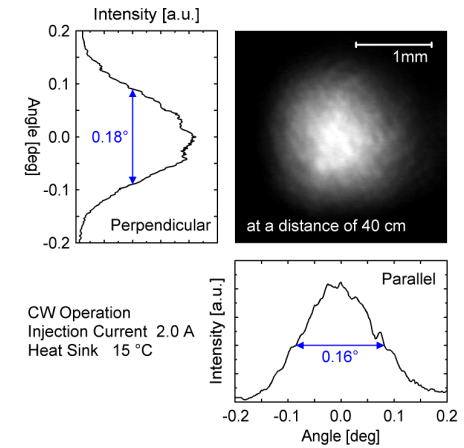
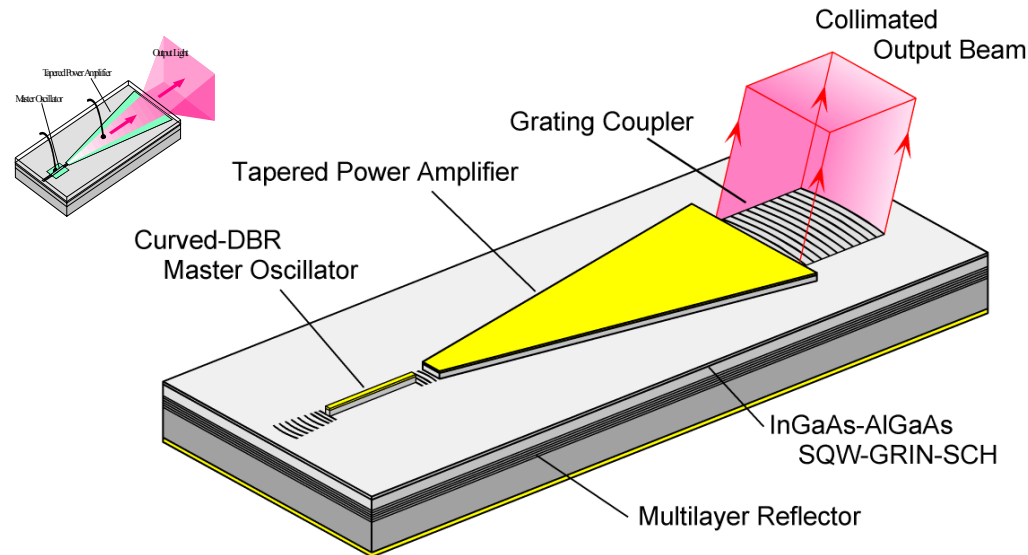
Monolithic Integrated-Optic Disc Pickup Head



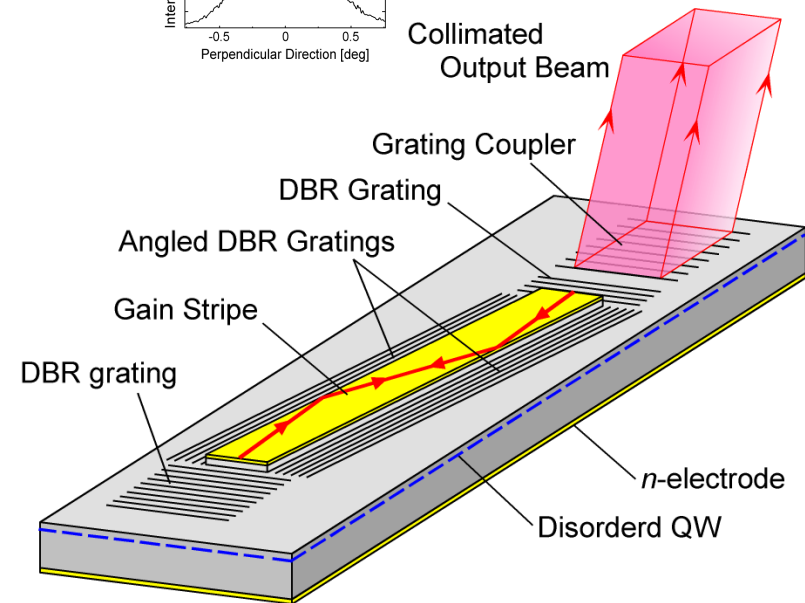
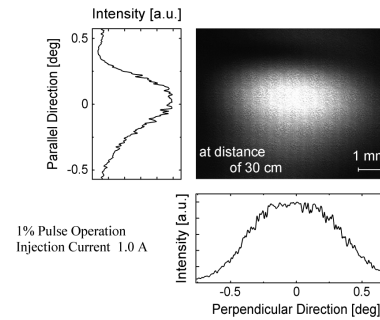
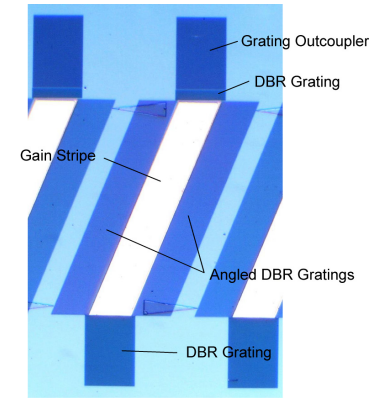
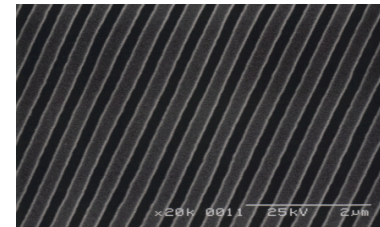
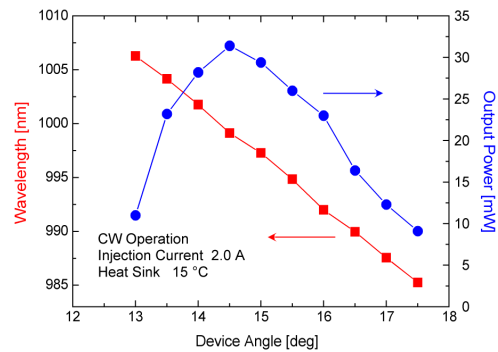
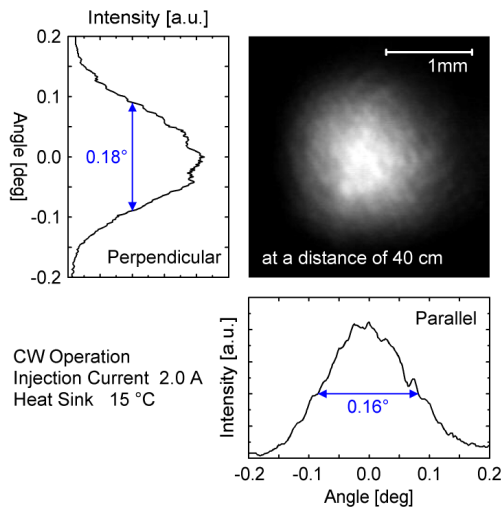
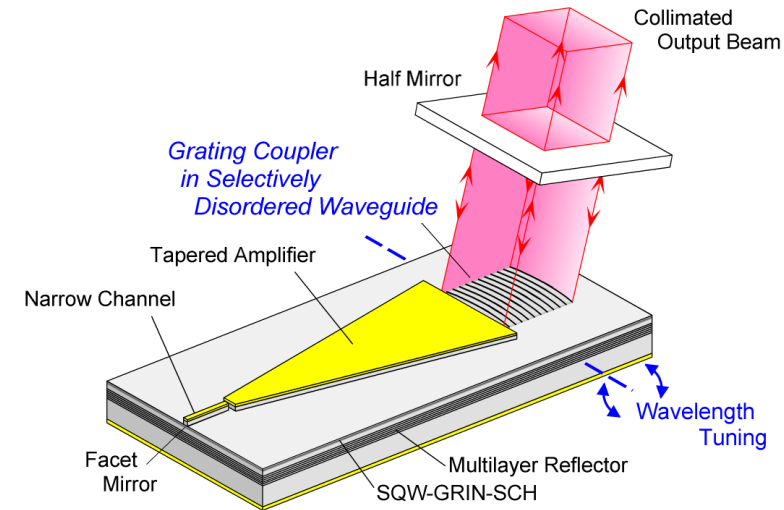
Monolithic Integrated-Optic Interferometer Position/Displacement Sensor

Integrated High-Power High Coherence Semiconductor Lasers

Master Oscillator Power Amplifier with integrated Outcoupler



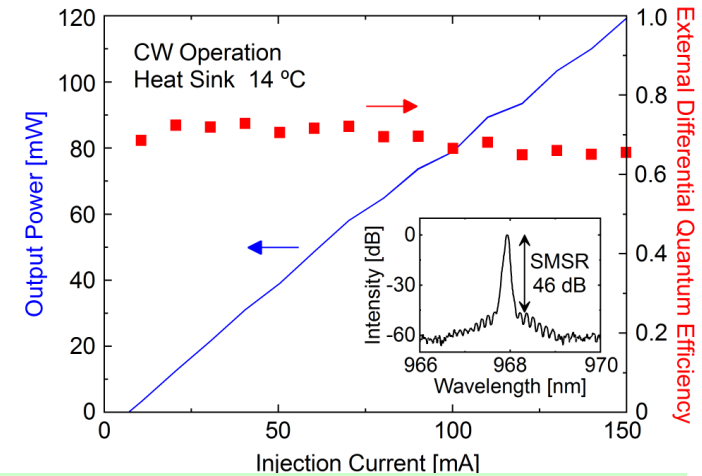
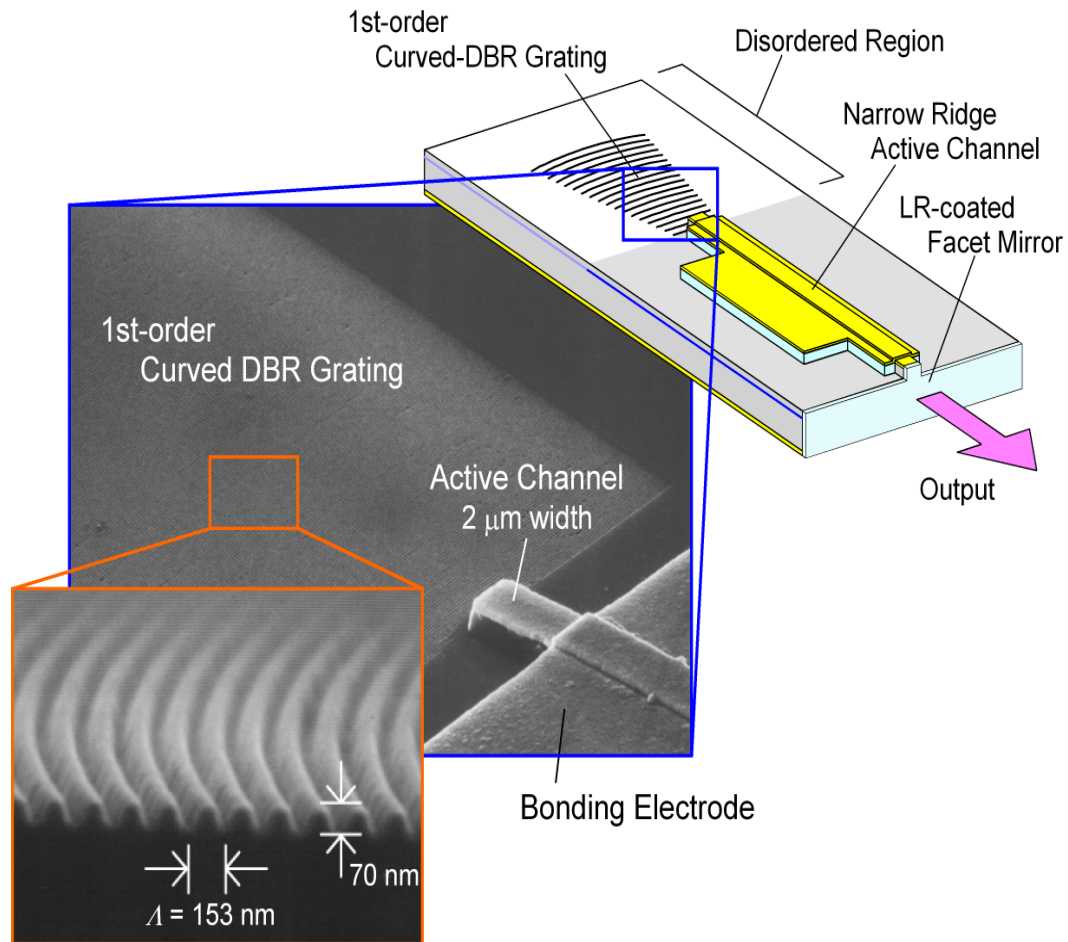
Integrated High-Power High Coherence Semiconductor Lasers



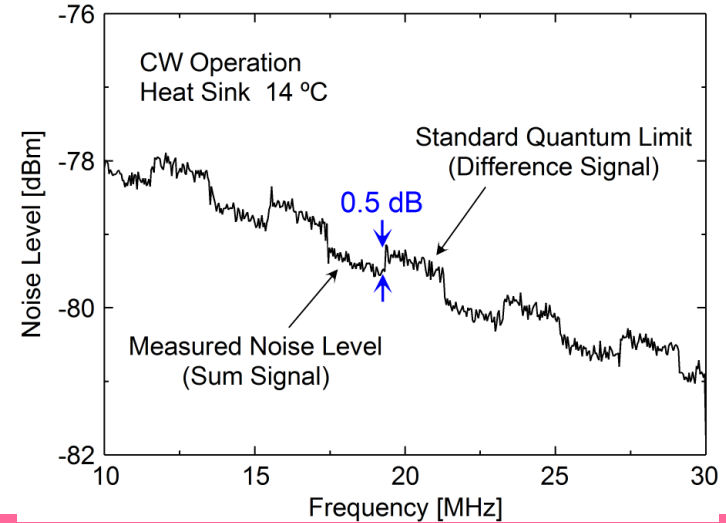
Extended Cavity Tunable Laser

Broad-Area DBR Laser

14InGaAs QW DBR Laser for Squeezed Light Generation



$$I_{th} = 7 \text{ mA} \quad \eta_d \sim 0.63 \quad \text{Max } I/I_{th} = 21$$



Generation of Squeezed Light

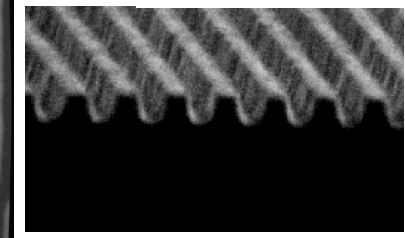
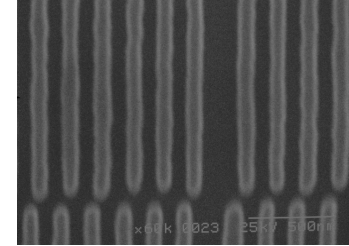
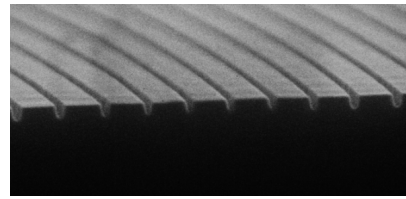
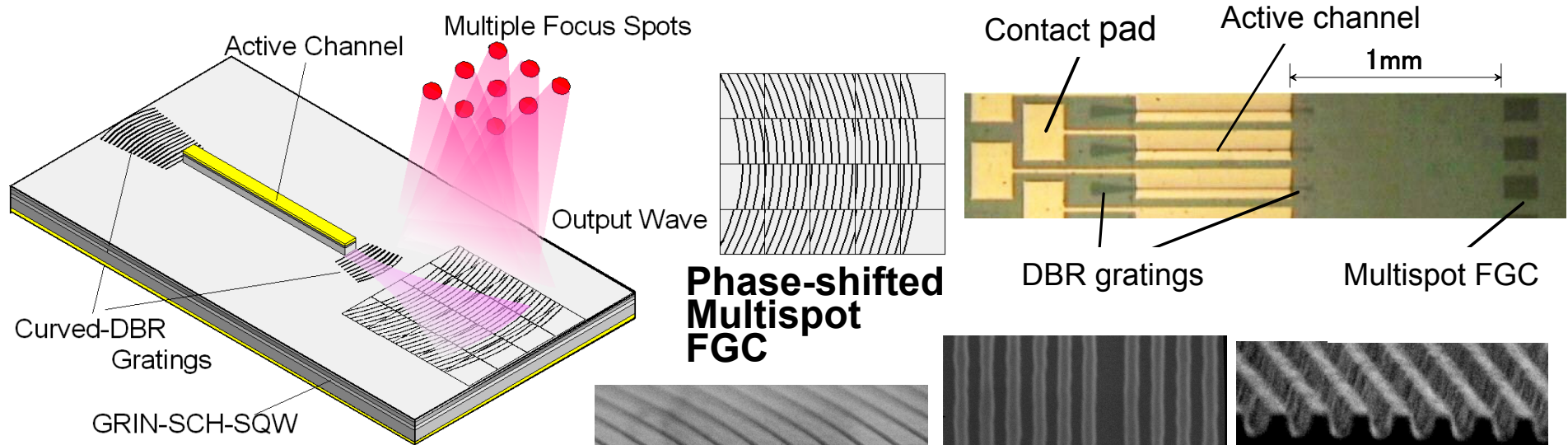
External Quantum Efficiency 74%

Side Mode Suppression 52 dB

Maximum Output Power 250 mW

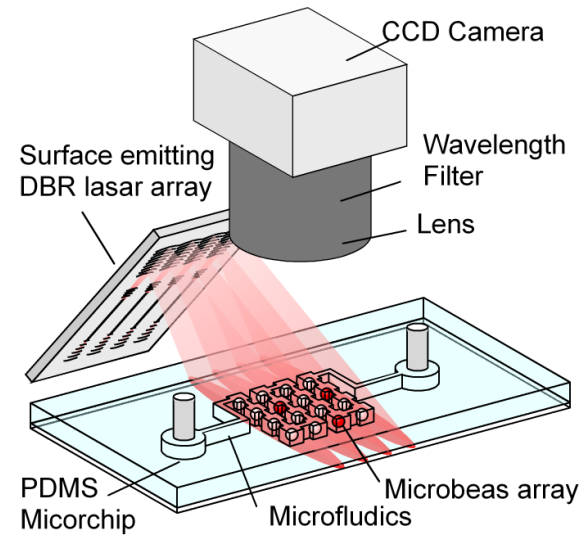
Accomplished

DBR laser with multispot focusing grating coupler

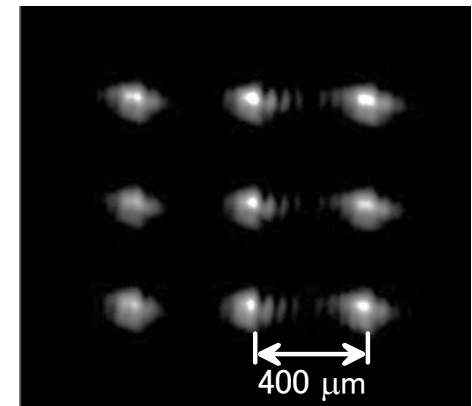
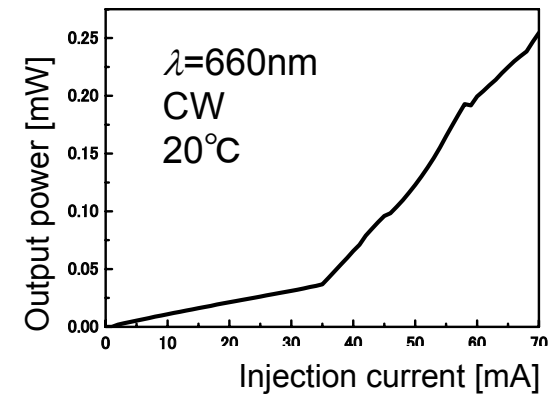


$\lambda \sim 191\text{nm}$

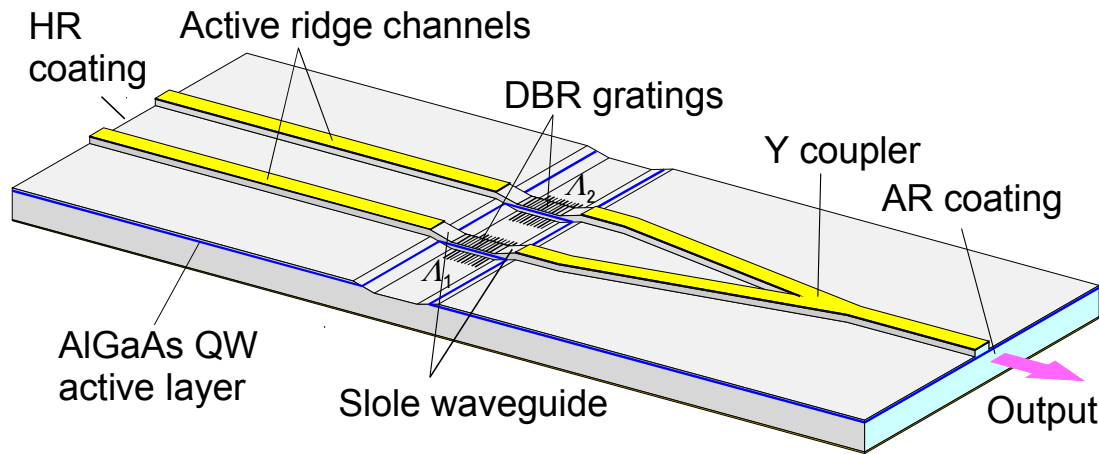
$d \sim 100\text{nm}$



Application to biosensing



Integrated twin DBR laser for THz wave generation



to GaAs photomixer

